

Notice of References Cited	Application/Control No. 10/692,029	Applicant(s)/Patent Under Reexamination SHAO ET AL.	
	Examiner Livius R. Cazan	Art Unit 3729	Page 1 of 2

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*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
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NON-PATENT DOCUMENTS

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